

74GTL1655A

16 BIT LVTTL TO GTL/GTL + UNIVERSAL BUS TRANSCEIVERS WITH LIVE INSERTION

- HIGH SPEED GTL/GTL+ UNIVERSAL TRANSCEIVER:
 - $t_{PD} = 4.6 \text{ ns (MAX.)} \text{ A to B at } V_{CC} = 3V$
- COMBINES D-TYPE LATCHES AND D-TYPE FLIP-FLOPS FOR OPERATION IN TRANSPARENT, LATCHED, OR CLOCKED MODE
- OPERATING VOLTAGE RANGE: V_{CC}(OPR) = 3.0V to 3.6V
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL}=24mA (MIN) at V_{CC} = 3V (A PORT)
- OUTPUT IMPEDANCE:
 - $I_{OL} = 100 \text{mA} \text{ (MIN)} \text{ at } V_{CC} = 3 \text{V (B PORT)}$
- HIGH-IMPEDANCE STATE DURING POWER UP AND POWER DOWN up to V_{CC}=BIASV_{CC}=1.5V PERMITT LIVE INSERTION
- B-PORT PRECHARGED BY BIASV_{CC} REDUCE NOISE ON THE LINE DURING LIVE INSERTION
- EDGE RATE-CONTROL INPUT CONFIGURES THE B-PORT OUTPUT RISE AND FALL TIMES
- BUS HOLD ON DATA INPUTS ELIMINATES THE NEED FOR EXTERNAL PULL-UP/ PULL-DOWN RESISTORS (A PORT)
- DISTRIBUTED V_{CC} AND GND PIN CONFIGURATION MINIMIZES HIGH-SPEED SWITCHING NOISE IN PARALLEL COMUNICATIONS
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 1655

DESCRIPTION

The 74GTL1655A devices are 16-bit high-drive (100mA), low-output-impedance universal bus transceivers designed for backplane applications. The 74GTL1655A devices provide live-insertion capability for backplane applications by tolerating active signals on the data ports when the devices are powered off. In addition, a biasing pin preconditions the GTL/GTL+ port to minimize disruption to an active backplane.

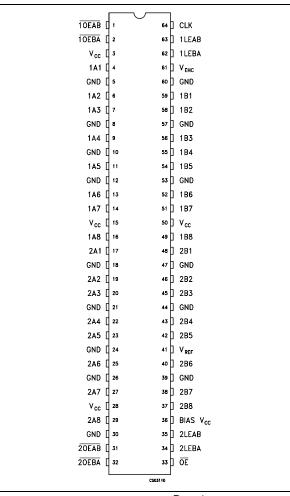
The edge rate-control (V_{ERC}) input is provided so the rise and fall time of the B outputs can be configured to optimize for various backplane loading conditions. Data flow in each direction is



Table 1: Order Codes

PACKAGE	T&R
TSSOP	74GTL1655ATTR

Figure 1: Pin Connection



Rev. 1

controlled by output-enable (\overline{OEAB} and \overline{OEBA}), latch-enable (LEAB and LEBA), and clock (CLK) inputs. For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLK is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When \overline{OEAB} is low, the outputs are active. When \overline{OEAB} is high, the outputs are in the high-impedance state. Data flow for B to A is similar to that of A to B, but uses \overline{OEBA} , LEBA, and CLK. The output enable (\overline{OE}) is used to disable both ports simultaneously.

Active bus-hold circuitry is provided on the A port to hold unused or floating data inputs at a valid logic level. When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, \overline{OE} should be tied to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

All input and output are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

Figure 2: Input And Output Equivalent Circuit

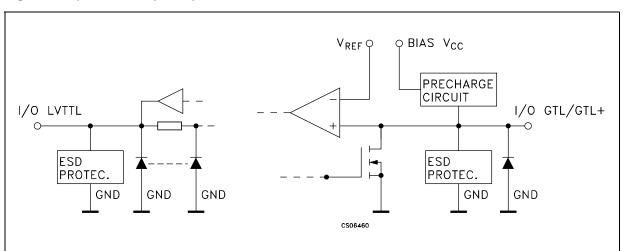


Table 2: Pin Description

PIN N°	SYMBOL	NAME AND FUNCTION
1, 2	1OEAB, 1OEBA	Output Enable Input
4, 6, 7, 9, 11, 13, 14, 16	1A1 to 1A8	Data Inputs/Outputs LVTTL
17, 19, 20, 22, 23, 25, 27, 29	2A1 to 2A8	Data Inputs/Outputs LVTTL
31, 32	2OEAB, 2OEBA	Output Enable Input
33	ŌE	Output Enable Input
34, 35	2LEBA, 2LEAB	Latch Enable
36	BIAS V _{CC}	Pre-Charge Supply Voltage
37, 38, 40, 42, 43, 45, 46, 48	2B8 to 2B1	Data Inputs/Outputs GTL/GTL+
41	V_{REF}	GTL Voltage Reference Input
49, 51, 52, 54, 55, 56, 58, 59	2A1 to 2A8	Data Inputs/Outputs GTL/GTL+
61	V _{ERC}	Edge Rate Control
62, 63	1LEBA, 1LEAB	Latch Enable
64	CLK	Clock Input (LOW to HIGH edge triggered)
5, 8, 10, 12, 18, 21, 24, 26, 30, 39, 44, 47, 53, 57, 60	GND	Ground (0V)
3, 15, 28, 50	V _{CC}	Positive Supply Voltage

Table 3: Function Table (1)

	INPUTS				MODE
OEAB	LEAB	CLK	Α	В	MODE
Н	Х	Х	Х	Z	Isolation
L	Н	X	L	L	Transparent
L	Н	X	Н	Н	Transparent
L	L		L	L	Registered
L	L		Н	Н	Registered
L	L	Н	X	B0 ⁽²⁾	Previous State
L	L	L	Х	B0 ⁽³⁾	Previous State

Table 4: Output Enable Truth Table

	INPUTS	OUTPUTS		
ŌĒ	OEAB	OEBA A PORT		B PORT
L	L	L	Active	Active
L	L	Н	Z	Active
L	Н	L	Active	Z
L	Н	Н	Z	Z
Н	X	Х	Z	Z

Table 5: B-Port Edge Rate Control (V_{ERC}) Truth Table

INPUT	r V _{ERC}	OUTPUT B PORT EDGE RATE
LOGIC LEVEL	NOMINAL VOLTAGE	OUT OF BY ON EDOL NATE
Н	V _{CC}	Slow
L	GND	Fast

¹⁾ A to B data flow is shown. B to A flow is similar, but uses $\overline{\text{OEBA}}$, LEBA and CLK
2) Output level before the indicated steady-state input conditions were established, provided that CLK was high before LEAB went low
3) Output level before the indicated steady-state input conditions were established

Figure 3: Logic Diagram

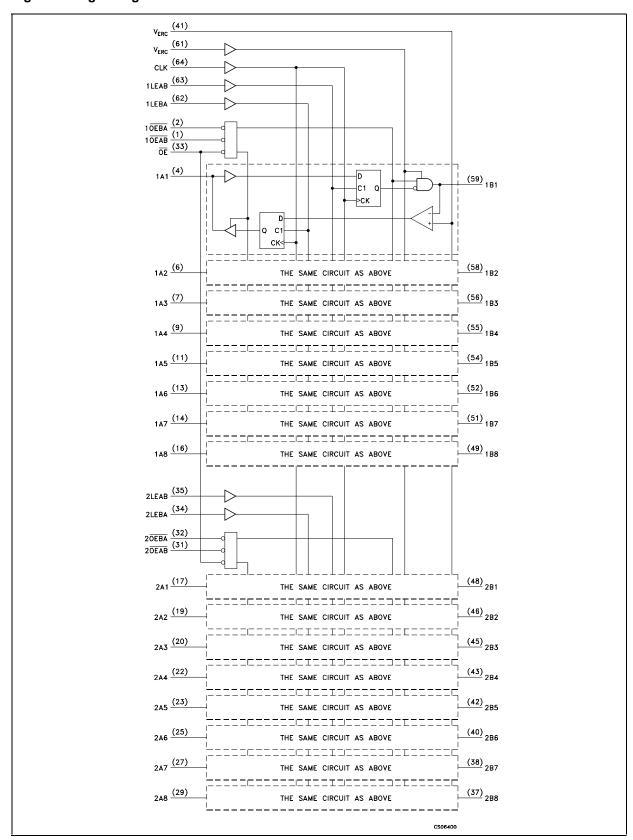


Table 6: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage, Bias V _{CC}	-0.5 to +4.6	V
V _{IA}	DC Input Voltage A Side, Control Input	-0.5 to +4.6	V
V _{IB}	DC Input Voltage B Side, V _{ERC} , V _{REF}	-0.5 to +4.6	V
V _{OA}	DC Output Voltage A Side	-0.5 to +4.6	V
V _{OB}	DC Output Voltage B Side	-0.5 to +4.6	V
I _{IK}	DC Input Diode Current	- 50	mA
I _{OK}	DC Output Diode Current	- 50	mA
I _{OA}	DC Output Current A Side	± 48	mA
I _{OB}	DC Output Current B Side in the Low State	200	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Rating are those value beyond which damage to the device may occur. Functional operation under these condition is not implied

Table 7: Recommended Operating Conditions

Cumb al	Parameter			Value			
Symbol	Parameter	Min.	Тур.	Max.	Unit		
V _{CC}	Supply Voltage		3.0	3.3	3.6	V	
V _{TT}	Termination Voltage	GTL	1.14	1.2	1.26	V	
		GTL+	1.35	1.5	1.65	V	
V _{REF}	Supply Voltage	GTL	0.74	0.8	0.87	V	
		GTL+	0.87	1	1.1	V	
V _I	Input Voltage	B port	0		V _{TT}	V	
		other	0		V _{CC}	V	
V _{IH}	High Level Input Voltage	B port	V _{REF} +0.05			V	
		other	2			V	
V _{IL}	Low Level Input Voltage	B port			V _{REF} -0.05	V	
		other			0.8	\ \ \	
I _{IK}	Input Clamp Current				-18	mA	
I _{OH}	High Level Output Current	A port			-24	mA	
1	Low Level Output Current	A port			24	A	
l _{OL}		B port			100	mA	
dt/dV _{CC}	Power -up ramp rate		200			μs/V	
T _{op}	Operating Temperature		-40		85	°C	

¹⁾ V_{TT} and R_{TT} can be adjusted to adapt backplane impedance if DC recommended I_{OL} ratings are not exceeded 2) V_{REF} can be adjusted to optimize noise margin (typ two-thirds V_{TT})

Table 8: DC Specifications

			Те	Test Condition Value				
Symbol	Parame	ter	V _{CC}		-	40 to 85 °C	•	Unit
			(V)		Min.	Тур.	Max.	
V _{IK}	High Level Inpu	ıt Voltage	3				-1.2	V
V _{OHA}	High Level Out	put	3 to 3.6	I _O =-100μA	V _{CC} -0.2			
	Voltage A Port		3	I _O =-12mA	2.4			V
			3	I _O =-24mA	2.2			
V _{OLA}	Low Level Outp	out	3 to 3.6	I _O =100μA			0.2	
	Voltage A Port		3	I _O =12mA			0.4	V
			3	I _O =24mA			0.55	
V _{OLB}	Low Level Outp	out	3	I _O =40mA			0.2	
	Voltage B Port		3	I _O =80mA			0.4	V
			3	I _O =100mA			0.5	
I _I	Input Current	Control	3.6	$V_I = V_{CC}$ or GND			±10	μΑ
		B Port	3.6	$V_I = V_{TT}$ or GND			±10	μΑ
I _{off}	Power Off Leak Current	age	0	$V_{I} \text{ or } V_{O} = 0 \text{ to } 3.6V$			±100	μΑ
I _{I(HOLD)}	Bus Hold A Port Input	t Input	3	V _I = 0.8V	75		20	
	Current		3	V _I = 2V	-75			μΑ
			3.6	$V_I = 0$ to V_{CC}			± 500	
I _{OZHB}	3-State Output Port	Current B	3.6	V _O = 1.5V			10	μА
l _{OZLB}	3-State Output Port	Current B	3.6	V _O = 0.4V			-10	μА
I _{OZ} (*)	3-State Output Port	Current A	3.6	$V_O = V_{CC}$ or GND			±10	μА
I _{OZPU**}	3-State Output Port	Current A	0 to 1.5	$V_O = 0.5 \text{ to } 3V$ OE = LOW			±50	μΑ
I _{OZPD**}	3-State Output Port	Current A	1.5 to 0	$V_O = 0.5 \text{ to } 3V$ $OE = LOW$			±50	μА
I _{CC}	Quiescent Sup Current	oly	3.6	$V_I = V_{CC}$ or GND $I_{O} = 0$		10	40	mA
ΔI_{CC}	Δ Supply Curre B port	nt except	3.6	$V_{IN} = V_{CC}$ or GND One input $V_{CC} = 0.6V$			1	mA
CI	Control Input C tance	apaci-		$V_{IN} = V_{CC}$ or GND		3	5	pF
Co	Input Capacitar			$V_O = V_{CC}$ or GND		5	6	pF
	Input Capacitar	nce B Port		10 100 01 011		6	8	Pi

^(*) For I/O ports, the parameter I $_{OZ}$ includes the input leakage current (**) Is also guaranteed when connecting BiasV $_{CC}$ with V $_{CC}$.

Table 9: Live Insertion Specifications

	Test Condition						
Symbol	Parameter	Vcc		-40 to 85 °C		;	Unit
		(V)		Min.	Тур.	Max.	
I _{CC} (Bias	Quiescent Bias Current	0 to 3.0	$V_{O(Bport)} = 0 \text{ to } 1.2V$			5	mA
V _{CC})		3 to 3.6	$V_{I(Bias\ Vcc)} = 3 \text{ to } 3.6 \text{V}$			10	μΑ
Vo	Output Voltage B Port	0	V _{I(Bias Vcc)} = 3.3V	1		1.2	V
I _O	Output Current B Port	0	$V_{O(Bport)} = 0.4V$ $V_{I(Bias\ Vcc)} = 3 \text{ to } 3.6V$	-1			μΑ
		0 to 3.6	OE = 3.3V			100	μΑ
		0 to 1.5	$\overline{OE} = 0 \text{ to } 3.3V$	•		100	μΑ

Table 10: AC Electrical Characteristics for GTL

(V_{CC}=3.3 \pm 0.3V, V_{TT}=1.2V, V_{REF}=0.8V, V_{ERC}=V_{CC} or GND)

Symbol	Parameter	Test Condition		Unit		
			Min.	Тур.	Max.	
f _{MAX}	Maximum Frequency		160			MHz
	A to B or B to A		100			IVIITZ
t _{PLH}	Propagation Delay Time	$V_{ERC}=V_{CC}$ R ₁ =12.5 Ω C _L =30pF	1.5		5.2	ns
t _{PHL}	A to B		1.5		6.2	115
t _{PLH}	Propagation Delay Time	$V_{ERC}=V_{CC}$ $R_L=12.5\Omega$ $C_L=30pF$	1.5		5.5	ns
t _{PHL}	CK to B		1.5		5.8	115
t _{PLH}	Propagation Delay Time	$V_{ERC}=V_{CC}$ $R_L=12.5\Omega$ $C_L=30pF$	1.5		5.8	no
t _{PHL}	LEAB to B		1.5		6.4	ns
t _{EN}	Enable Delay Time OEAB or OE to B	$V_{ERC}=V_{CC}$ R _L =12.5 Ω C _L =30pF	1.5		5.4	
t _{DIS}	Disable Delay Time OEAB or OE to B		1.5		6.2	ns
t _{PLH}	Propagation Delay Time	V_{ERC} =GND R _L =12.5 Ω C _L =30pF	1.5		4.3	
t _{PHL}	A to B		1.5		4.6	ns
t _{PLH}	Propagation Delay Time	V_{ERC} =GND R _L =12.5 Ω C _L =30pF	1.5		4.3	
t _{PHL}	CK to B		1.5		4.9	ns
t _{PLH}	Propagation Delay Time	V_{ERC} =GND R _L =12.5 Ω C _L =30pF	1.5		4.9	
t _{PHL}	LEAB to B		1.5		4.8	ns
t _{EN}	Enable Delay Time OEAB or OE to B	V_{ERC} =GND R _L =12.5 Ω C _L =30pF	1.5		4.8	
t _{DIS}	Disable Delay Time OEAB or OE to B		1.5		4.2	ns
t _{PLH}	Propagation Delay Time	$R_L=500\Omega$ $C_L=50pF$	1.5		4.7	
t _{PHL}	B to A		1.5		4.8	ns
t _{PLH}	Propagation Delay Time	R _L =500Ω C _L =50pF	1.5		4	,,,,
t _{PHL}	CK to A		1.5		4	ns
t _{PLH}	Propagation Delay Time	R _L =500Ω C _L =50pF	1.5		4	
t _{PHL}	LEBA to A		1.5		3.7	ns

		Test Condition			Value		
Symbol	Parameter			-40 to 85 °C			Unit
				Min.	Тур.	Max.	
t _{EN}	Enable Delay Time OEBA or OE to A	$R_L = 500\Omega R_1 = 500$	0ΩC _L =50pF	1		4.6	
t _{DIS}	Disable Delay Time OEBA or OE to A			1		6.1	- ns
t _{SU}	t _{SU} Set-up Time	Data before clock	ζ	2.7			
		Data before LE	Ck High	2.8			ns
			Ck Low	2.6			
t _H	Hold Time	Data after clock		0.4			ns
		Data after LE Ck	High or LOW	0.9			1115
t _W	Pulse duration	LE High		3			no
		CK High or Low		3			ns
Slew rate	!	V _{ERC} =V _{CC}				1	ns/V
	transition (0.6 to 1.3V)	V _{ERC} =GND				1	115/V
t _{sk}	Skew between drivers (in	Switching in the	same direction			1	no
	the same package)	Switching in any direction				1	ns

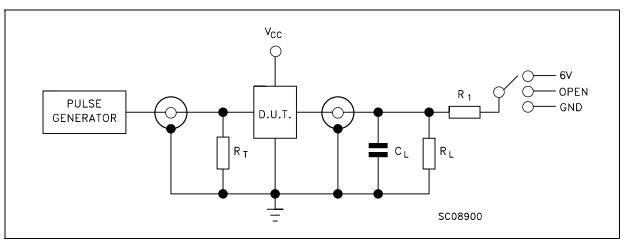
Table 11: AC Electrical Characteristics for GTL+

(V_{CC}=3.3 \pm 0.3V, V_{TT}=1.5V, V_{REF}=1.0V, V_{ERC}=V_{CC} or GND)

						Unit
Symbol	Parameter	Test Condition	-40 to 85 °C			
			Min.	Тур.	Max.	
f _{MAX}	Maximum Frequency		160			MHz
	B to A or A to B		160			IVITZ
t _{PLH}	Propagation Delay Time	$V_{ERC}=V_{CC}$ $R_{L}=12.5\Omega$ $C_{L}=30pF$	1.5		5.1	200
t _{PHL}	A to B		1.5		6.5	ns
t _{PLH}	Propagation Delay Time	$V_{ERC}=V_{CC}$ R _L =12.5 Ω C _L =30pF	1.5		5.4	
t _{PHL}	CK to B		1.5		6.2	ns
t _{PLH}	Propagation Delay Time LEAB to B	$V_{ERC}=V_{CC}$ R _L =12.5 Ω C _L =30pF	1.5		5.7	
t _{PHL}			1.5		6.7	ns
t _{EN}	Enable Delay Time OEAB or OE to B	$V_{ERC}=V_{CC}$ R _L =12.5 Ω C _L =30pF	1.5		5.5	
t _{DIS}	Disable Delay Time OEAB or OE to B		1.5		5.8	ns
t _{PLH}	Propagation Delay Time	V_{ERC} =GND R _L =12.5 Ω C _L =30pF	1.0		4.3	
t _{PHL}	A to B		1.0		4.9	ns
t _{PLH}	Propagation Delay Time	V_{ERC} =GND R _L =12.5 Ω C _L =30pF	1.0		4.0	
t _{PHL}	CK to B		1.0		5.5	ns
t _{PLH}	Propagation Delay Time	V_{ERC} =GND R _L =12.5 Ω C _L =30pF	1.0		4.0	
t _{PHL}	LEAB to B		1.0		5.4	ns
t _{EN}	Enable Delay Time OEAB or OE to B	V_{ERC} =GND R _L =12.5 Ω C _L =30pF	1.0		5.1	
t _{DIS}	Disable Delay Time OEAB or OE to B		1.0		4.9	ns

		Test Condition		Value -40 to 85 °C			Unit
Symbol	Parameter						
				Min.	Тур.	Max.	1
t _{PLH}		R_L =500 Ω C_L =50pF		1.5		4.8	ns
t _{PHL}	B to A			1.5		4.7	
t _{PLH}		R_L =500 Ω C_L =50pF		1.5		4.4	ns
t _{PHL}	CK to A			1.5		4.1	
t _{PLH}	Propagation Delay Time	$R_L=500\Omega$ $C_L=50pF$		1.5		4	ns
t _{PHL}	LEBA to A			1.5		3.7	
t _{EN}	Enable Delay Time OEBA or OE to A	R_L =500Ω R_1 =500Ω C_L =50pF		1		4.2	- ns
t _{DIS}	Disable Delay Time OEBA or OE to A			1		6.1	
Slew rate	ate Slew rate B output both transition (0.6 to 1.3V)	$V_{ERC}=V_{CC}$ $R_{L}=12.5\Omega$ $C_{L}=30pF$				1	ns/V
		V_{ERC} =GND R _L =12.5 Ω C _L =30pF				1	
t _W	Pulse duration	LE High		3			ns
		CK High or Low		3			
t _{SU}	Set-up Time	Data before clock		2.7			
		Data before LE	Ck High	2.8			ns
			Ck Low	2.6			
t _H	Hold Time	Data after clock		0.4			- ns
		Data after LE Ck High or LOW		0.9			
t _{sk}	Skew between drivers (in	Switching in the same direction				1	- ns
	the same package)	Switching in any direction				1	

Figure 4: Test Circuit For "A" Outputs

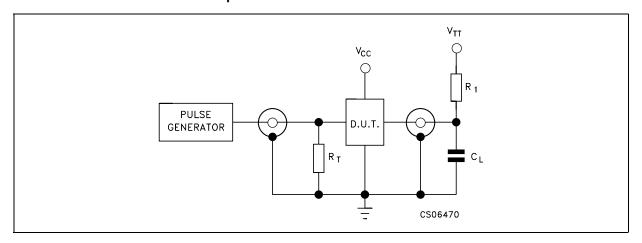


Test	Switch
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6V
t _{PZH} , t _{PHZ}	GND

 C_L = 50pF or equivalent (includes jig and probe capacitance) $R_L=R_1$ = 500 Ω or equivalent $R_T=Z_{OUT}$ of pulse generator (typically 50 Ω) t_r = t_f <=2.5ns

47/

Table 12: Test Circuit For "B" Outputs



 C_L = 30pF or equivalent (includes jig and probe capacitance)

 $R_L = R1 = 12.5\Omega$ or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

 $t_r = t_f <= 2.5 \text{ns}$

Figure 5: Waveform - Pulse Duration (A Port, Control Pin)

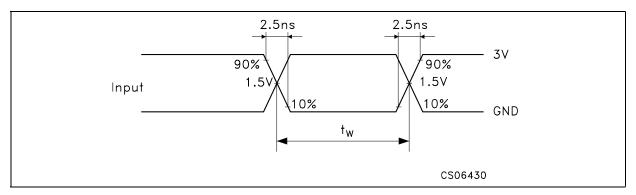


Figure 6: Waveform - Clock To B Port Propagation Delay Time

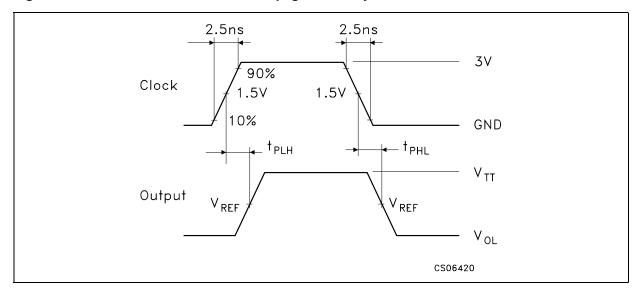


Figure 7: Waveform - Clock To A Port Propagation Delay Time

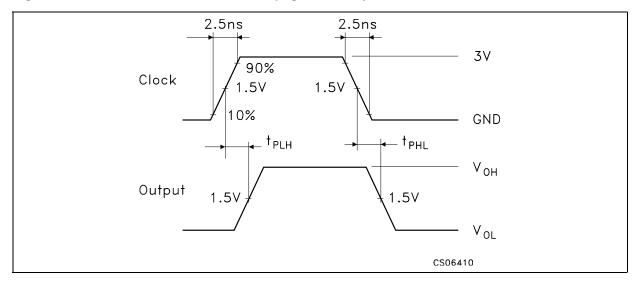


Figure 8: Waveform - Setup And Hold Time

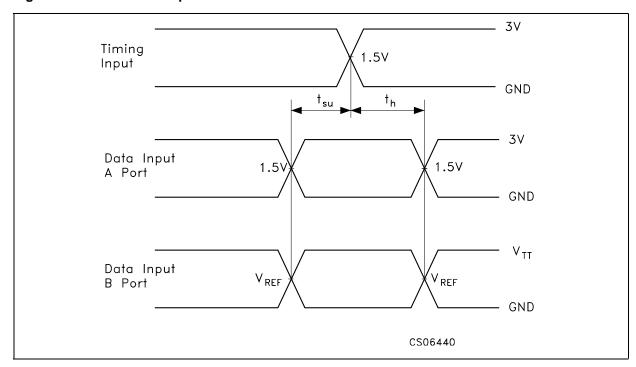
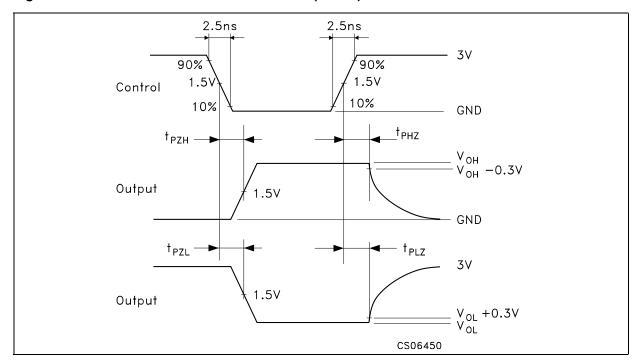
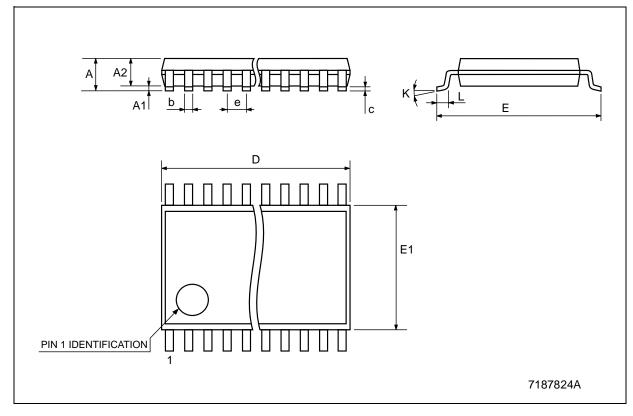


Figure 9: Waveform - Enable And Disable Time (A Port)



TSSOP64 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			1.1			0.043
A1	0.05		0.15	0.002		0.006
A2		0.9			0.035	
b	0.17		0.27	0.0067		0.011
С	0.09		0.20	0.0035		0.0079
D	16.9		17.1	0.665		0.673
Е		8.1			0.318	
E1	6.0		6.2	0.236		0.244
е		0.5 BSC			0.0197 BSC	
К	0°		8°	0°		8°
L	0.50		0.75	0.020		0.030



Tape & Reel TSSOP64 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
Т			30.4			1.197
Ao	8.7		8.9	0.342		0.350
Во	17.2		17.4	0.677		0.685
Ko	1.4		1.6	0.055		0.063
Po	3.9		4.1	0.153		0.161
Р	11.9		12.1	0.468		0.476

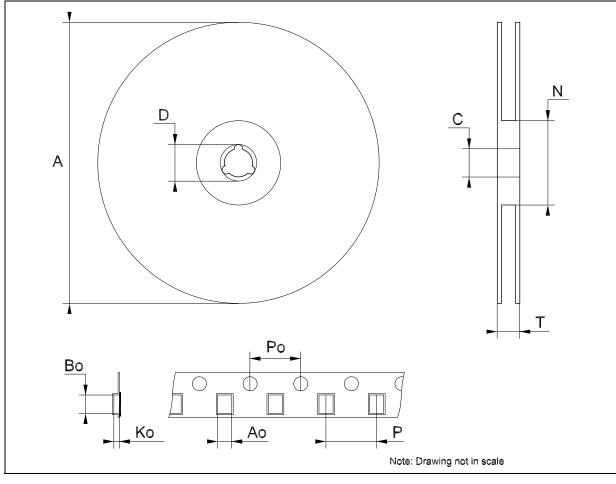


Table 13: Revision History

Date	Revision	Description of Changes
18-Oct-2004	1	First Release.

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics All other names are the property of their respective owners

© 2004 STMicroelectronics - All Rights Reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America www.st.com



This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.